ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE2330
Silicon NPN Transistor
High Gain Amp w/Internal Zener Diode

Features:

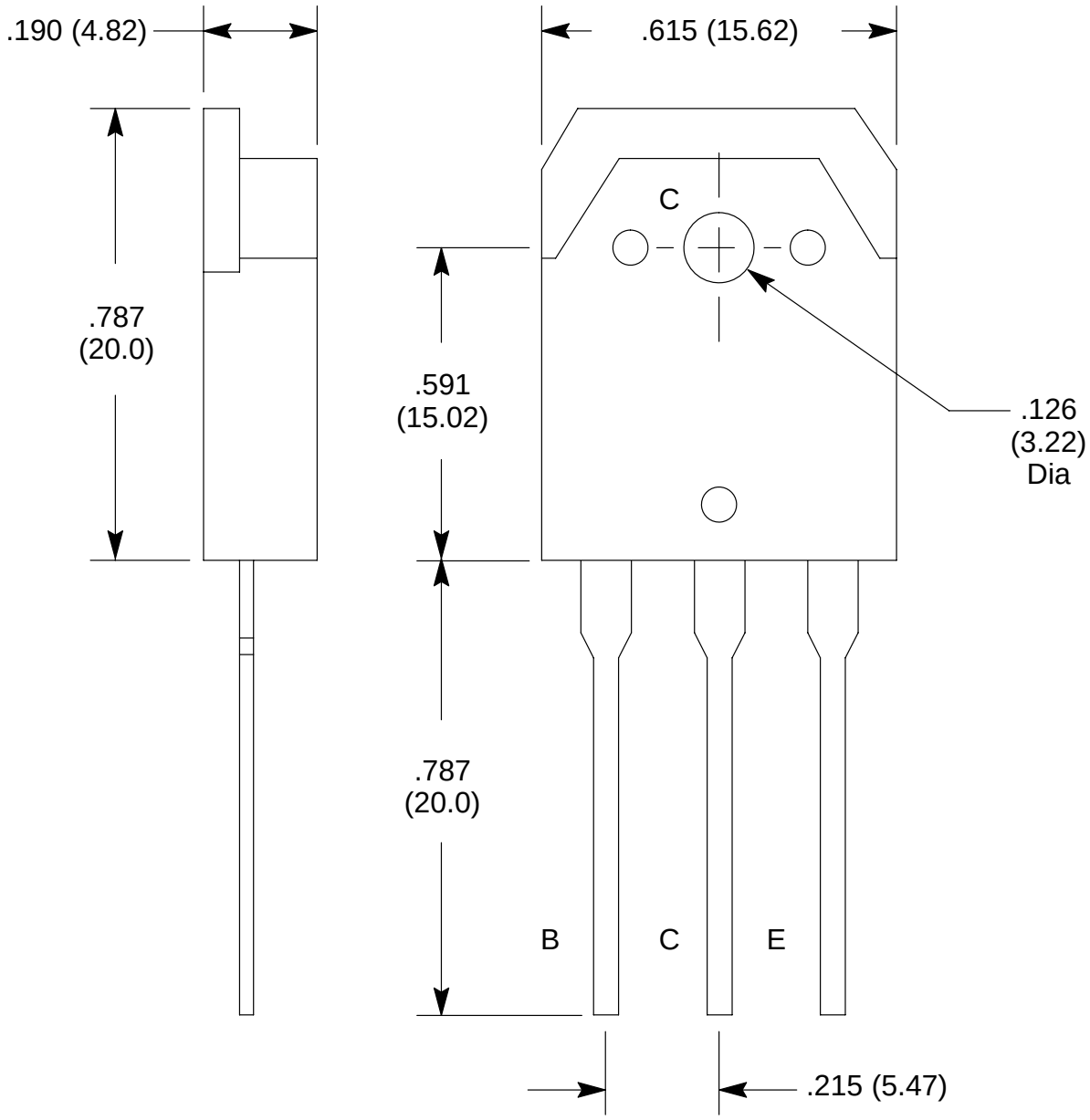
- Excellent Wide Safe Operating Area
- Included Avalanche Diode
- High DC Current Gain
- High Collector Power Dissipation Capability

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} . . . . . 55 (+15, –10) V
Collector–Emitter Voltage, V_{CEO} . . . . . 55 (+15, –10) V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C
  Continuous 4A
  Peak 20A
Collector Dissipation (T_C = +25°C), P_C 80W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 10mA, I_E = 0	45	55	70	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CBO}$	I_C = 100mA, I_B = 0	45	55	70	V
Emitter Cutoff Current	I_{EBO}	V_{EB} = 5V, I_C = 0	–	–	10	μA
DC Current Gain	h_{FE}	V_{CE} = 5V, I_C = 500mA	500	1000	2500	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 500mA, I_B = 2mA	–	–	2.0	V
		I_C = 1A, I_B = 20mA	–	–	3.0	V
Base–Emitter Voltage	V_{BE}	V_{CE} = 5V, I_C = 500mA	0.50	0.65	0.80	V
Allowable Energy	E_T		80	–	–	W.sec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C
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